- High V_{CEO}, V_{CEO}=80V
- High I_C, I_C=1A (DC)
- Low $V_{CE\ (sat)}$
- Complementary to 2SB1260

Parameter	Symbol	Rating	Unit
Collector - Base Voltage	V_{CBO}	120	V
Collector - Emitter Voltage	V_{CEO}	80	
Emitter - Base Voltage	V_{EBO}	5	
Collector Current - Continuous	I_C	1	A
Collector Current - Pulse	I_{CP}	2	
Collector Power Dissipation	P_C	0.5	W
		2	
Junction Temperature	T_J	150	℃
Storage Temperature Range	T_{stg}	-55 to 150	

Parameter	Symbol	Test Conditions	Min	Typ	Max	Unit
Collector- base breakdown voltage	V_{CBO}	I_C= 100 uA， I_E= 0	120			
Collector- emitter breakdown voltage	V_{CEO}	I_C= 1 mA，I_B= 0	80			
Emitter - base breakdown voltage	V_{EBO}	I_E= 100 uA， I_C= 0	5			
Collector-base cut-off current	I_{CBO}	V_{CB}= 100 V , I_E= 0			1	
Emitter cut-off current	I_{EBO}	V_{EB}= 4V , I_C=0			0.5	
Collector-emitter saturation voltage	V_{CE}					

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